

What is claimed is:

1. A method of manufacturing a nitrogen-based semiconductor layer, comprising the steps of:
growing the nitrogen-based semiconductor layer on a provisional substrate which forms a heterojunction with the nitrogen-based semiconductor layer; and
etching out the provisional substrate by the use of an etchant for the provisional substrate to leave only the nitrogen-based semiconductor layer as a nitrogen-based semiconductor substrate.
2. A method as claimed in claim 1, further comprising, before the etching step, the step of:
covering the nitrogen-based semiconductor layer with a protection layer against the etchant;
the etching step being carried out with the nitrogen-based semiconductor layer covered with the protection layer to etch out the provisional substrate and to thereby leave the nitrogen-based semiconductor layer and the protection layer.
3. A method as claimed in claim 1, wherein the nitrogen-based semiconductor layer is formed by a nitrogen-based semiconductor thick film.
4. A method as claimed in claim 1, wherein the nitrogen-based semiconductor layer implements a nitrogen-based semiconductor device structure.
5. A method as claimed in claim 1, further comprising the step of:
processing the nitrogen-based semiconductor substrate into a nitrogen-based semiconductor device after the provisional substrate is etched out.

6. A method as claimed in claim 2, further comprising the step of: processing the nitrogen-based semiconductor substrate into a nitrogen-based semiconductor device after the provisional substrate is etched out.

7. A method as claimed in claim 6, wherein the nitrogen-based semiconductor device has an electrode formed by the protection layer.

8. A method as claimed in claim 1, wherein the provisional substrate is a sapphire substrate while the etchant is formed by a mixed solution of phosphoric acid and sulfuric acid or another mixed solution including the phosphoric acid and the sulfuric acid.

9. A method as claimed in claim 2, wherein the protection layer is formed by at least one material selected from a group consisting of Au, Pt, Ti-Au, Pd-Au, Ni-Au, Ti-Pt-Au, AuZn, and AuGe.

10. A method as claimed in claim 1, wherein the nitrogen-based semiconductor layer includes either $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 1$) or $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 1$).

11. A method as claimed in claim 1, wherein the nitrogen-based semiconductor layer includes at least two components selected from a group consisting of $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 1$), $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 1$), and $\text{Al}_x\text{In}_y\text{Ga}_{1-x-y}\text{N}$ ($0 \leq x + y \leq 1$).

12. A method as claimed in claim 8, wherein the sapphire is etched out by the use of the etchant kept at a temperature not lower than 300°C.

13. A method as claimed in claim 4, wherein the nitrogen-based semiconductor device structure forms a semiconductor laser, a light emitting diode, and/or a field effect transistor.

14. A method as claimed in claim 1, further comprising the step of:

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polishing the nitrogen-based semiconductor layer on its surface
faced to the provisional substrate so as to flatten the surface.

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